

## Abstract

### Microelectronic structure

A microelectronic structure is proposed in which an adhesion layer (20) is situated between a base substrate (5) and a barrier layer (25, 30). Said adhesion layer improves the adhesion of the barrier on the base substrate, in particular to insulation layers situated there. Microelectronic structures of this type are preferably used in semiconductor memories.

Figure 1e

# List of reference symbols

5	Base substrate
8	Polysilicon layer
9	Metal silicide layer
10	Contact hole/opening
15	Surface of the base substrate
20	Adhesion layer
25	Oxygen-containing iridium layer
30	Oxygen barrier layer/iridium dioxide layer
32	Side regions
35	Noble metal layer/platinum layer/metal-containing electrode layer
40	Dielectric metal-oxide-containing layer/STB layer
45	Further noble metal layer/platinum layer
50	Silicon oxide layer
55	TEOS layer/silicon nitride layer
65	Metal silicide
70	Selection transistor
75	Storage capacitor
80/85	Doped regions
90	Silicon substrate
95	Gate electrode
100	Gate dielectric
105	Lateral insulation webs
110	Insulation layer
115	Bottom electrode